

### KSC2334

# **High Speed Switching Industrial Use** • Complement to KSA1010



# **NPN Epitaxial Silicon Transistor**

Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

1.Base 2.Collector 3.Emitter

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	150	V
V <sub>CEO</sub>	Collector-Emitter Voltage	100	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
I <sub>C</sub>	Collector Current (DC)	7	А
I <sub>CP</sub>	*Collector Current (Pulse)	15	А
I <sub>B</sub>	Base Current (DC)	3.5	А
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	40	W
	Collector Dissipation (T <sub>A</sub> =25°C)	1.5	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

<sup>\*</sup> PW≤300μs, Duty Cycle≤10%

### Electrical Characteristics TC=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
V <sub>CEO</sub> (sus)	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 5A, I <sub>B1</sub> = 0.5A, L = 1mH	100		V
V <sub>CEX</sub> (sus)1	Collector-Emitter Sustaining Voltage	$I_C = 5A$ , $I_{B1} = -I_{B2} = 0.5A$ $V_{BE}(off) = -5V$ , $L = 180\mu H$ , Clamped	100		V
V <sub>CEX</sub> (sus)2	Collector-Emitter Sustaining Voltage	$I_C = 10A$ , $I_{B1} = 1A$ , $I_{B2} = -0.5A$ , $V_{BE}(off) = -5V$ , $L = 180\mu H$ , Clamped	100		V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 100, I_{E} = 0$		10	μΑ
I <sub>CER</sub>	Collector Cut-off Current	$V_{CE} = 100V, R_{BE} = 51\Omega@T_{C} = 125^{\circ}C$		1	mA
I <sub>CEX1</sub> I <sub>CEX2</sub>	Collector Cut-off Current	$V_{CE} = 100V, V_{BE}(off) = -1.5V$ $V_{CE} = 100V, V_{BE}(off) = -1.5V$ @ $T_{CE} = 125^{\circ}C$		10 1	μA mA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$		10	μΑ
h <sub>FE1</sub> h <sub>FE2</sub> h <sub>FE3</sub>	* DC Current Gain	$V_{CE} = 5V, I_{C} = 0.5A$ $V_{CE} = 5V, I_{C} = 3A$ $V_{CE} = 5V, I_{C} = 5A$	40 40 20	240	
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage	$I_C = 5A, I_B = 0.5A$		0.6	V
V <sub>BE</sub> (sat)	* Base-Emitter Saturation Voltage	$I_C = 5A, I_B = 0.5A$		1.5	V
t <sub>ON</sub>	Turn On Time	$V_{CC} = 50V, I_{C} = 5A$		0.5	μs
t <sub>STG</sub>	Storage Time	$I_{B1} = -I_{B2} = 0.5A$		0.5	μs
t <sub>F</sub>	Fall Time	$R_L = 10\Omega$		1.5	μs

<sup>\*</sup> Pulse Test: PW≤350μs, Duty Cycle≤2%Pulsed

### **h**<sub>FE</sub> Classification

Classification	R	0	Y
h <sub>FE2</sub>	40 ~ 80	70 ~ 140	120 ~ 240

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# **Typical Characteristics**

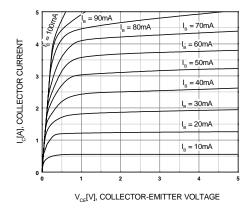


Figure 1. Static Characteristic

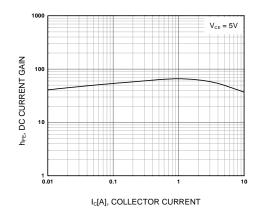


Figure 2. DC current Gain

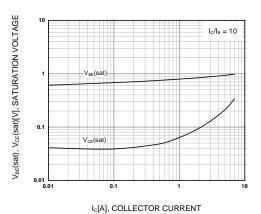


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

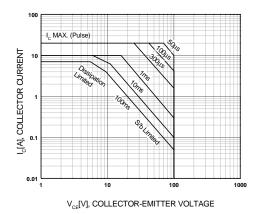


Figure 4. Safe Operating Area

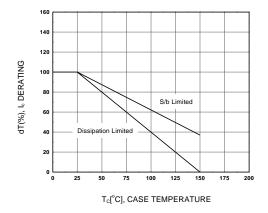


Figure 5. Derating Curve of Safe Operating Areas

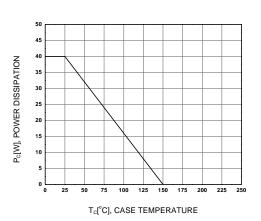
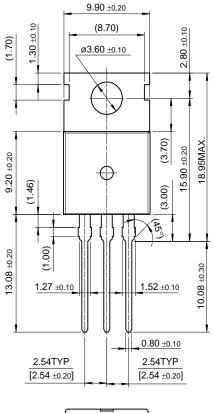


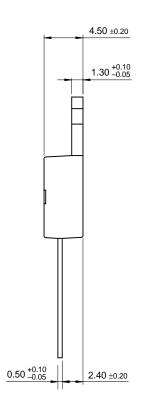
Figure 6. Power Derating

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# **Package Demensions**

# TO-220







Dimensions in Millimeters

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